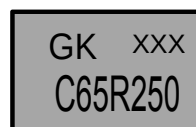


Features

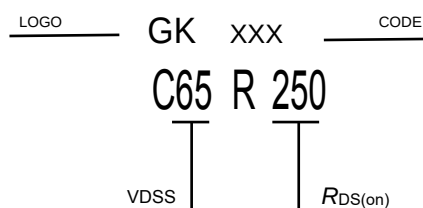
Ultra low $R_{DS(on)}$
Ultra low gate charge (typ. $Q_g=28.2nC$)
100% UIS tested
RoHS compliant

V_{DSS} 650 V
 I_D 15 A
 $R_{DS(on)}$ 0.25 Ω

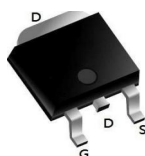


Applications

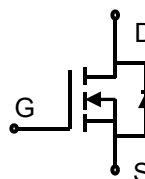
Power factor correction (PFC).
Switched mode power supplies (SMPS).
Uninterruptible power supply (UPS).



TO-252



Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	650	V
Continuous drain current ¹⁾ ($T_C = 25^\circ\text{C}$) ($T_C = 100^\circ\text{C}$)	I_D	15	A
		9.5	A
Pulsed drain current ²⁾	I_{DM}	45	A
Gate-Source voltage	V_{GSS}	± 30	V
Avalanche energy, single pulse ³⁾	E_{AS}	281.6	mJ
Power Dissipation	P_D	158	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$
Continuous diode forward current	I_S	15	A
Diode pulse current	$I_{S,pulse}$	45	A

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	650	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	2.5	3.5	4.5	V
Drain cut-off current	I _{DSS}	V _{DS} =650V, V _{GS} =0 V, T _j =25°C	-	-	1	μA
Gate leakage current, Forward	I _{GSSF}	V _{GS} =30V, V _{DS} =0 V	-	-	100	nA
Gate leakage current, Reverse	I _{GSSR}	V _{GS} =-30V, V _{DS} =0 V	-	-	-100	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =10V, I _D =7.5A	-			
		T _j = 25°C	-	0.25	0.28	Ω
		T _j = 150°C	-	0.62	-	
Gate resistance	R _G	f=1 MHz, open drain	-	5.71	-	Ω
Dynamic characteristics						
Input capacitance	C _{iss}	V _{DS} =100V, V _{GS} =0V, f=250kHz	-	1203.9	-	pF
Output capacitance	C _{oss}		-	42.78	-	
Reverse transfer capacitance	C _{rss}		-	0.61	-	
Turn-on delay time	t _{d(on)}	V _{DD} =400V, I _D =7.5A R _G = 10Ω, V _{GS} =10V	-	58.7	-	ns
Rise time	t _r		-	13.3	-	
Turn-off delay time	t _{d(off)}		-	54.8	-	
Fall time	t _f		-	7.4	-	
Gate charge characteristics						
Gate to source charge	Q _{gs}	V _{DD} =520V, I _D =7.5A, V _{GS} =0 to 10 V	-	6.3	-	nC
Gate to drain charge	Q _{gd}		-	12.1	-	
Gate charge total	Q _g		-	28.2	-	
Gate plateau voltage	V _{plateau}		-	5.44	-	V
Reverse diode characteristics						
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =7.5A	-	-	1.1	V
Reverse recovery time	t _{rr}	V _R =400V, I _F =7.5A, dI _F /dt=100 A/μs	-	262	-	ns
Reverse recovery charge	Q _{rr}		-	2552.2	-	nC
Peak reverse recovery current	I _{rrm}		-	21.02	-	A

Notes:

- Limited by maximum junction temperature and duty cycle.
- Limited by maximum junction temperature, maximum duty cycle is 0.75.
- $I_{AS}=3.2A, L=55mH, V_{DD}=60V$, Starting $T_J=25^{\circ}\text{C}$.
- The value of R_{thJA} is measured by placing the device in a still air box which is one cubic foot.

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.79	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient, minimal Footprint ⁴⁾	$R_{\theta JA}$	62	$^{\circ}\text{C}/\text{W}$
Soldering temperature, wave soldering only allowed at leads. (1.6mm from case for 10s)	T_{sold}	260	$^{\circ}\text{C}$

RATING AND CHARACTERISTIC CURVES

Figure 1. Typ. Output Characteristics

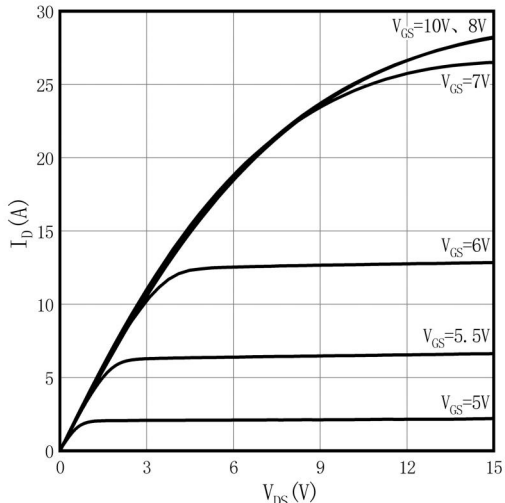


Figure 2. Transfer Characteristics

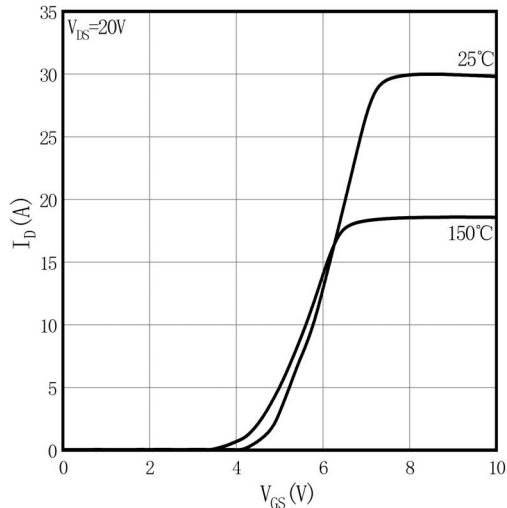


Figure 3. On-Resistance vs. Drain Current

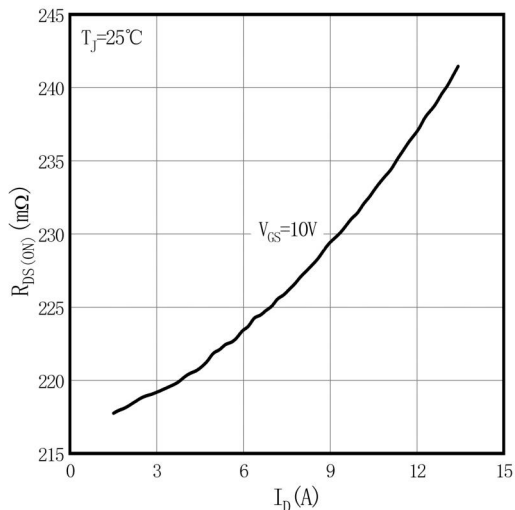


Figure 4. On-Resistance vs. Temperature

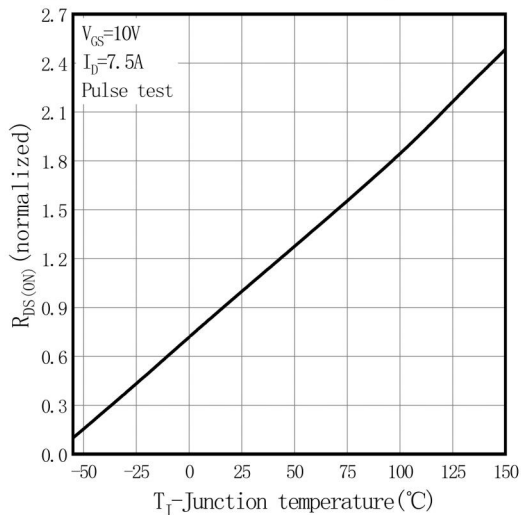


Figure 5. Breakdown Voltage vs. Temperature

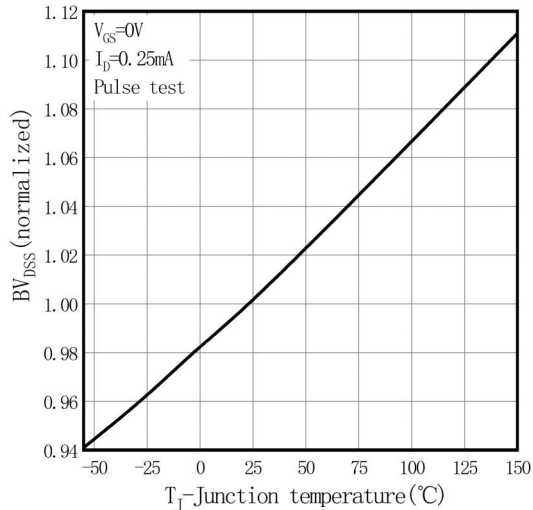
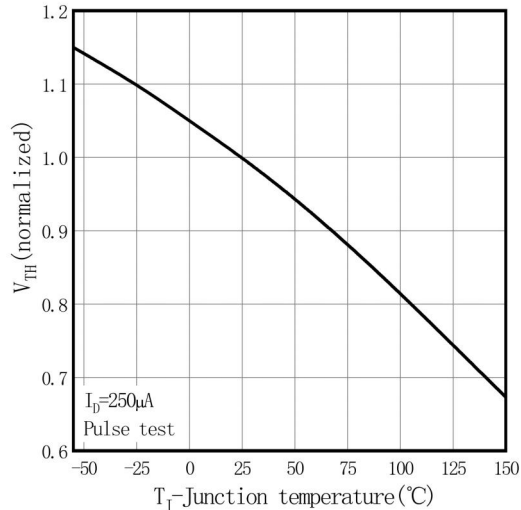


Figure 6. Threshold Voltage vs. Temperature



RATING AND CHARACTERISTIC CURVES

Figure 7.Body-Diode Characteristics

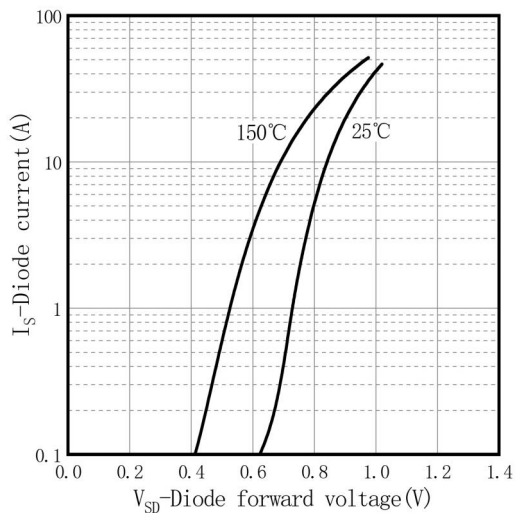


Figure 8.Capacitance Characteristics

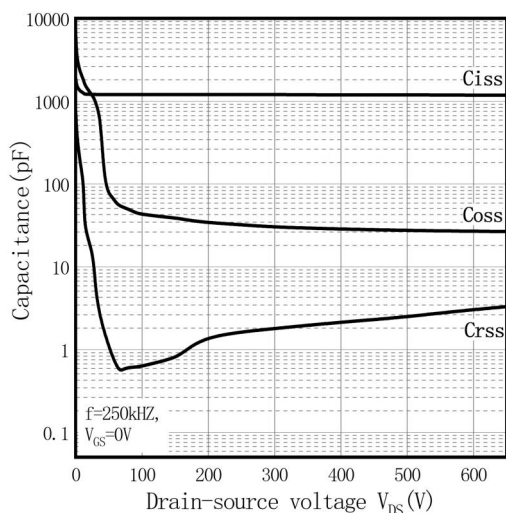


Figure 9.Gate Charge Characteristics

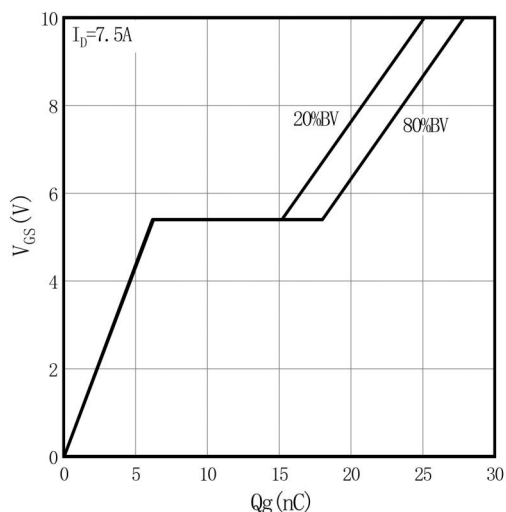


Figure 10.Drain Current Derating

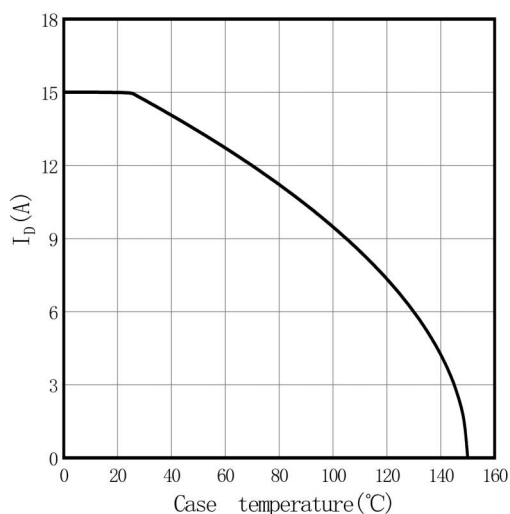
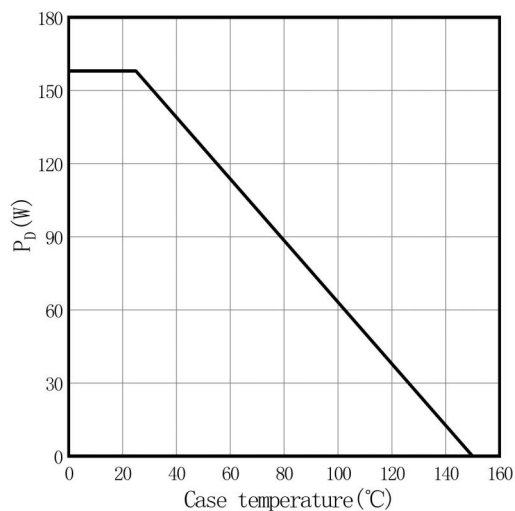
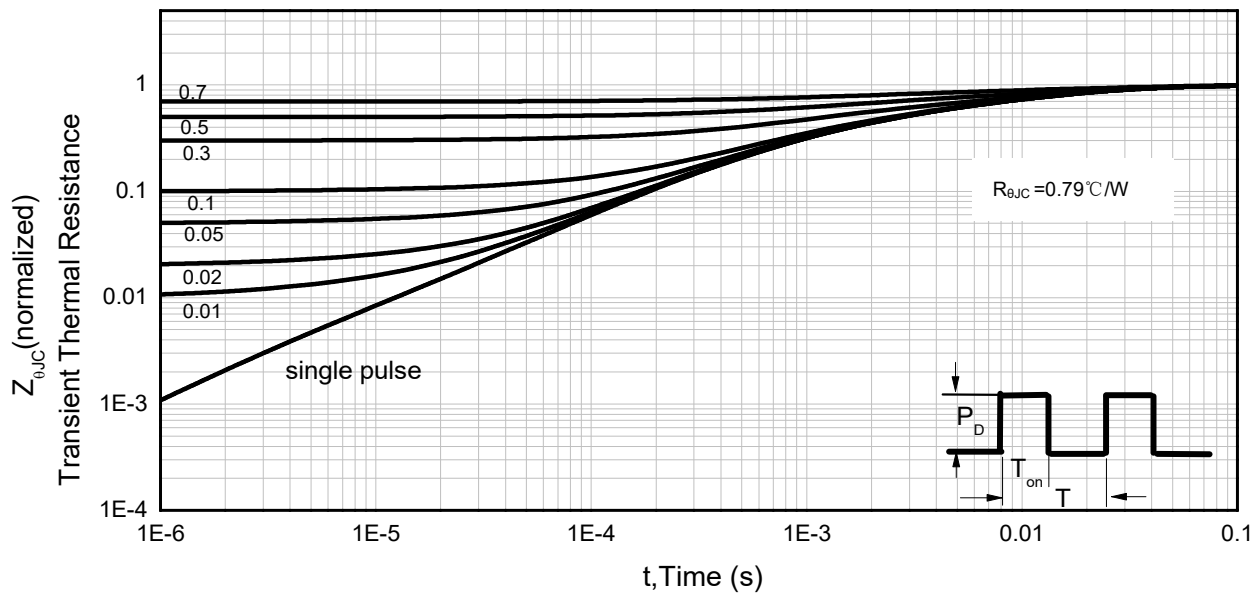


Figure 11.Power Dissipation vs.Temperature



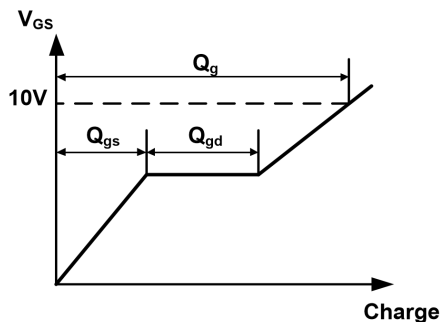
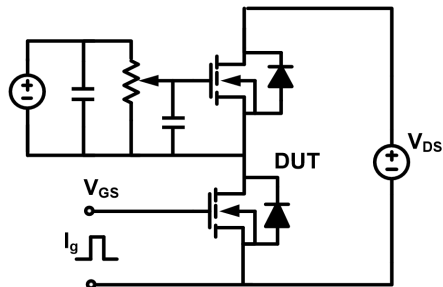
RATING AND CHARACTERISTIC CURVES

Figure 13. Normalized Maximum Transient Thermal Impedance (R_{thJC})

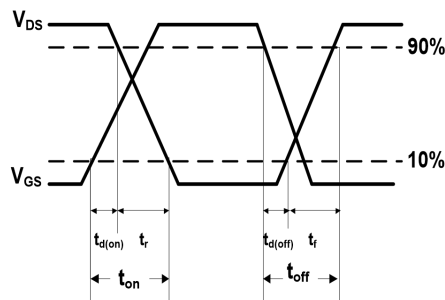
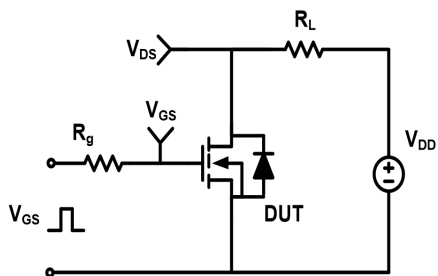


Test Circuit

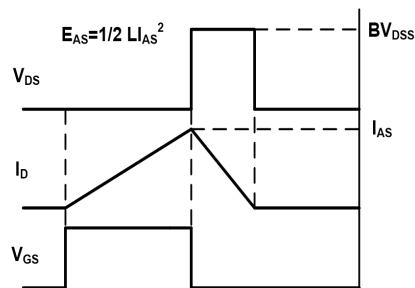
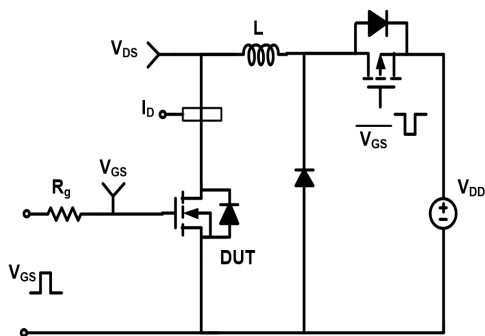
Gate Charge Test Circuit & Waveform



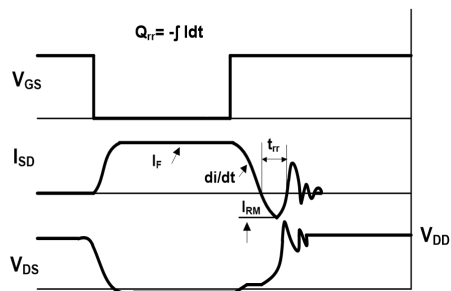
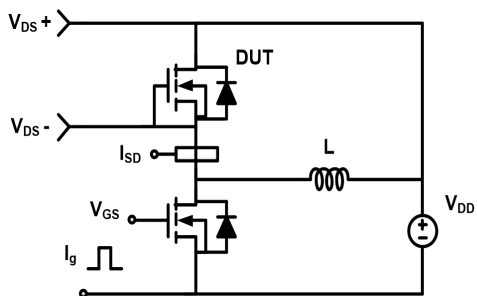
Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform

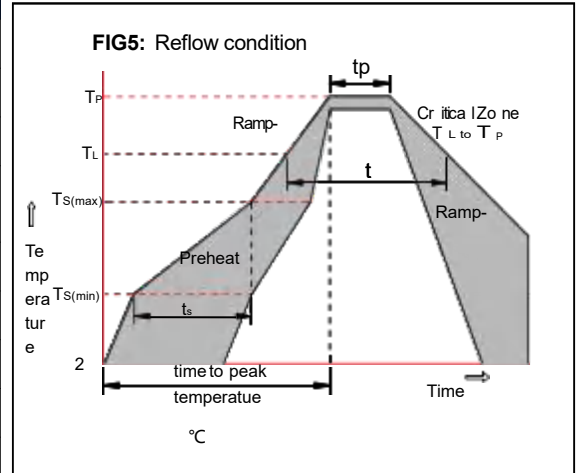


Diode Recovery Test Circuit & Waveform



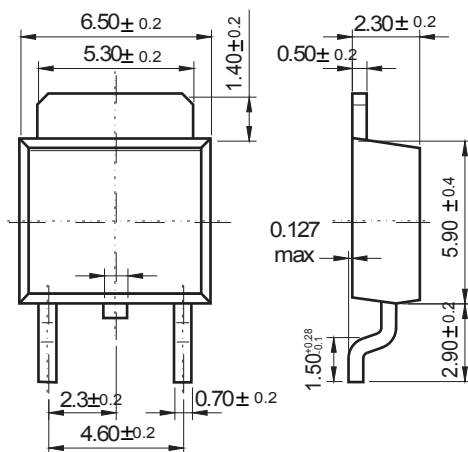
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 °C
	-Temperature Max($T_{s(max)}$)	+200 °C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3 °C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 °C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217 °C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5) °C
Time within 5 °C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6 °C/sec. Max
Time 25 °C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260 °C

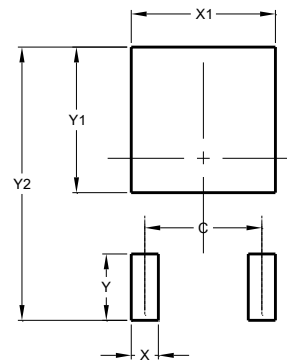


Package Dimensions & Suggested Pad Layout

TO-252



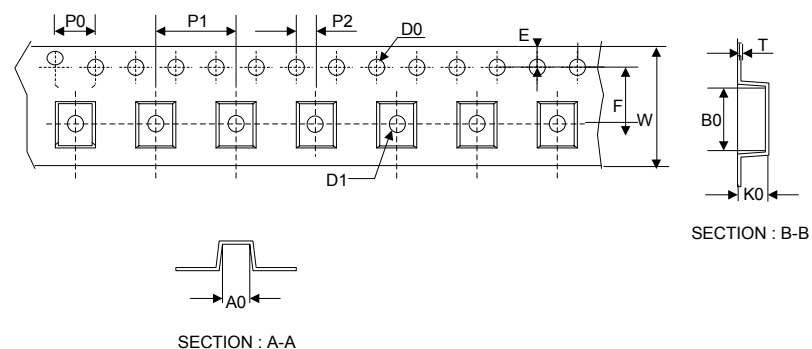
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

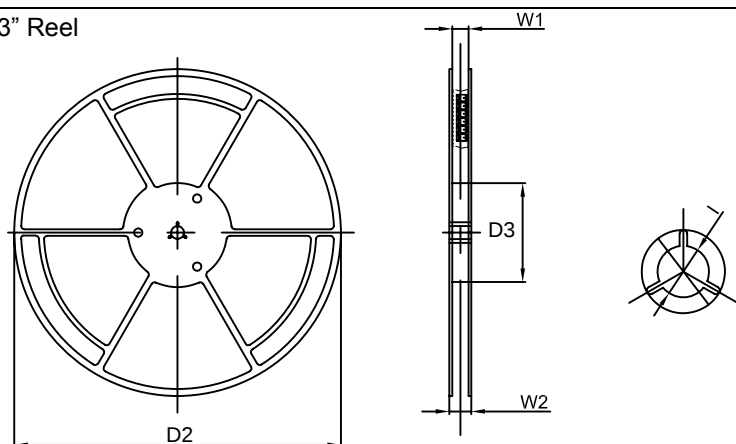
Tape & reel specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

13" Reel



Quantity: 2500PCS